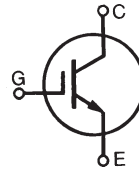


HiPerFAST™ IGBT

B2-Class High Speed IGBTs

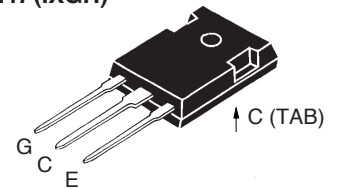
IXGH 32N90B2
IXGT 32N90B2

$$\begin{aligned} V_{CES} &= 900 \text{ V} \\ I_{C25} &= 64 \text{ A} \\ V_{CE(sat)} &= 2.7 \text{ V} \\ t_{fi \text{ typ}} &= 150 \text{ ns} \end{aligned}$$

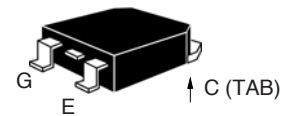


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	900	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	900	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	64	A
I_{C110}	$T_C = 110^\circ\text{C}$	32	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	200	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10 \Omega$ Clamped inductive load @ $\leq 600\text{V}$	$I_{CM} = 64$	A
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Plastic body for 10 s		260	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10Nm/lb.in.	
Weight		TO-247	6 g
		TO-268	4 g

TO-247 (IXGH)



TO-268 (IXGT)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- High frequency IGBT
- High current handling capability
- MOS Gate turn-on - drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Advantages

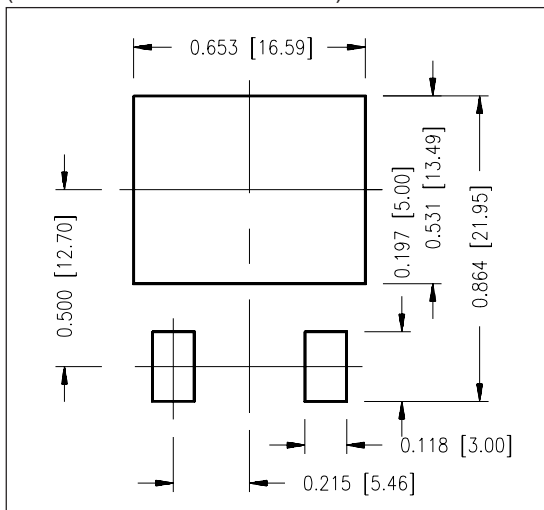
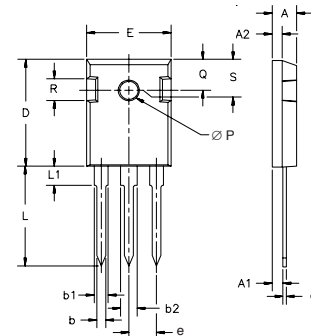
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		50 μA
		$T_J = 150^\circ\text{C}$		750 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15 \text{ V}$		2.2	2.7 V
		$T_J = 125^\circ\text{C}$	2.1	V

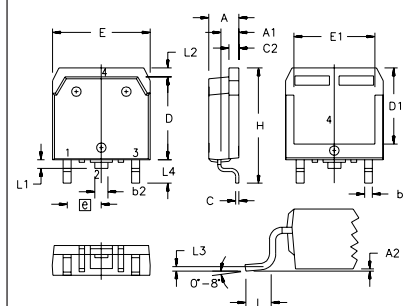
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$I_C = I_{C110} A$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	18	28	S	
C_{ies} C_{oes} C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1790	pF	
			121	pF	
			49	pF	
Q_g Q_{ge} Q_{gc}	$I_C = I_{C110}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		89	nC	
			15	nC	
			34	nC	
$t_{d(on)}$ t_{ri} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C110}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 720\text{ V}$, $R_G = R_{off} = 5\ \Omega$		20	ns	
			22	ns	
			260	400	ns
			150		ns
			2.6	4.5	mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C110} A$, $V_{GE} = 15\text{ V}$ $V_{CE} = 720\text{ V}$, $R_G = R_{off} = 5\ \Omega$		20	ns	
			22	ns	
			0.5		mJ
			3.8		mJ
			360		ns
			330		ns
		5.75		mJ	
R_{thJC} R_{thCS}	(TO-247)			0.42 KW KW	
		0.25			

Note 1

 Note 1: E_{on} measured with a DSEP 30-12A ultrafast diode clamp.

Min. Recommended Footprint
 (Dimensions in inches and mm)

TO-247 AD Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

Fig. 1. Output Characteristics
@ 25 °C

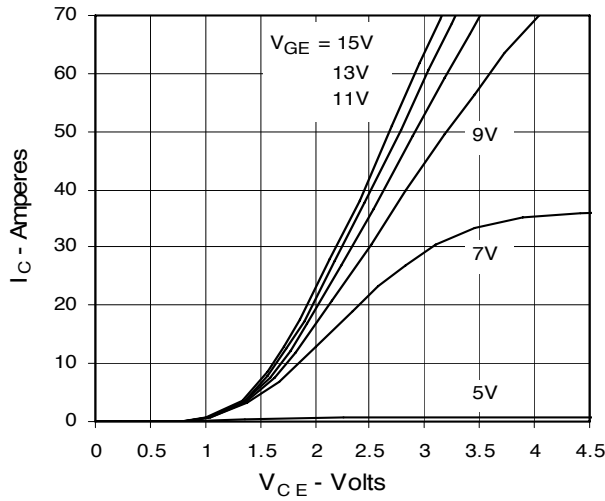


Fig. 2. Extended Output Characteristics
@ 25 °C

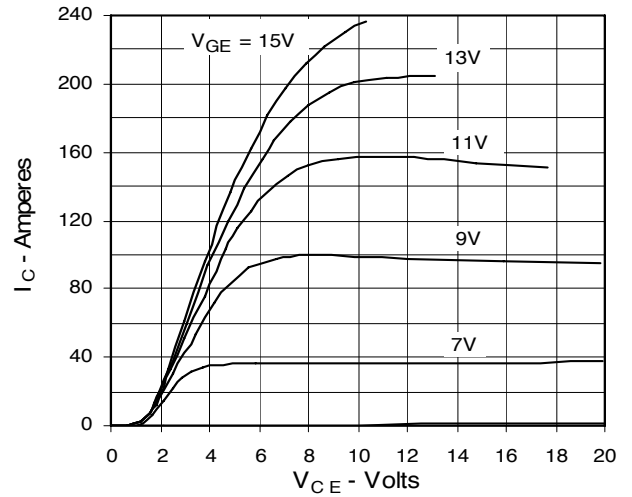


Fig. 3. Output Characteristics
@ 125 °C

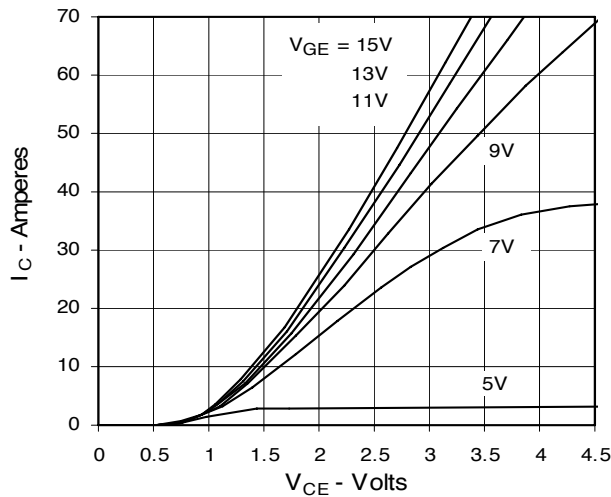


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

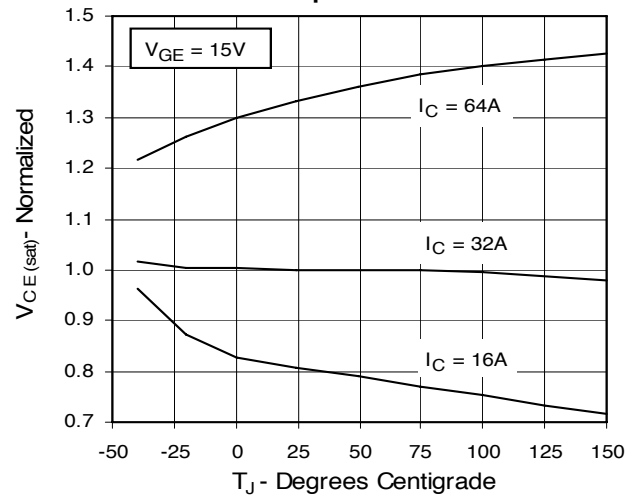


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

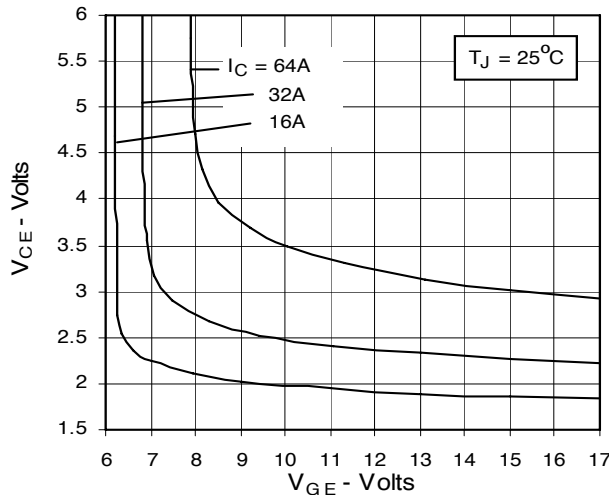


Fig. 6. Input Admittance

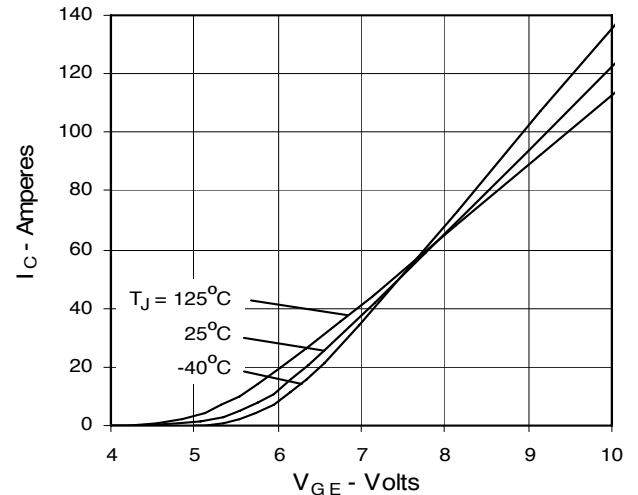


Fig. 7. Transconductance

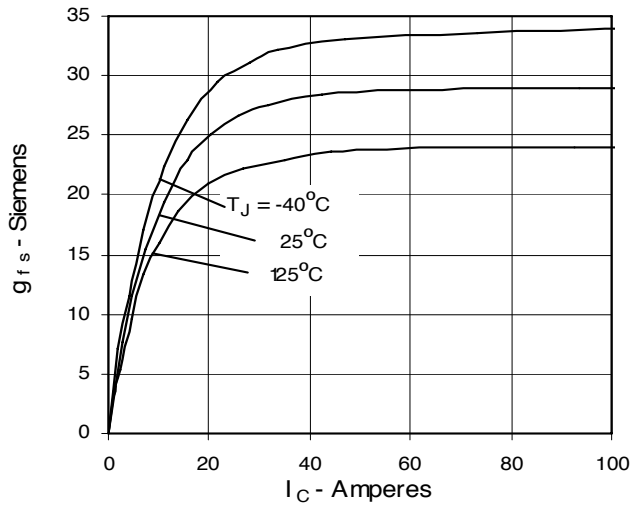


Fig. 8. Gate Charge

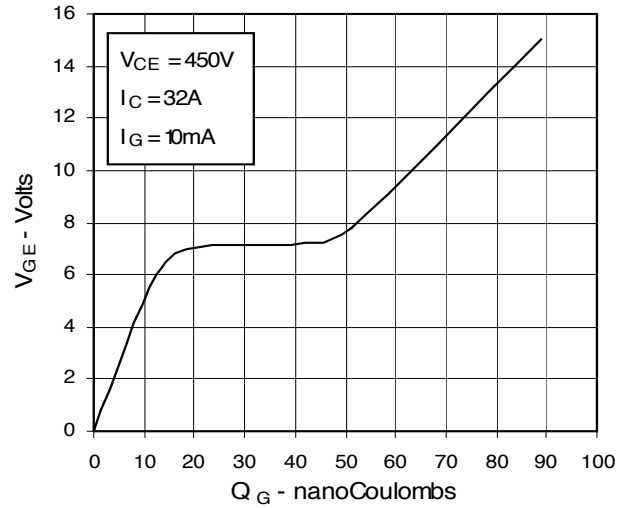


Fig. 9. Capacitance

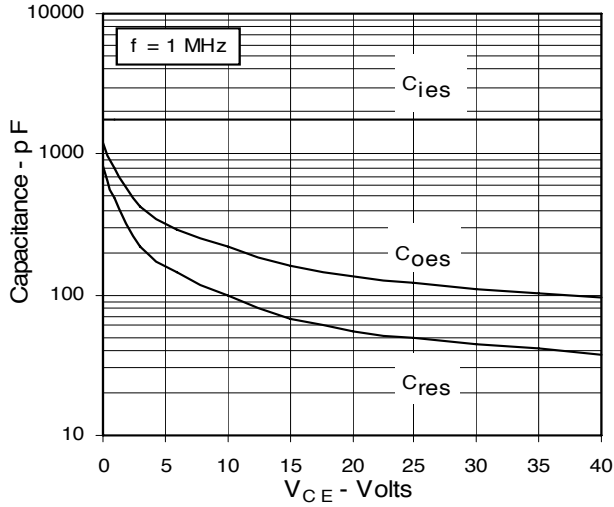


Fig. 10. Reverse-Bias Safe Operating Area

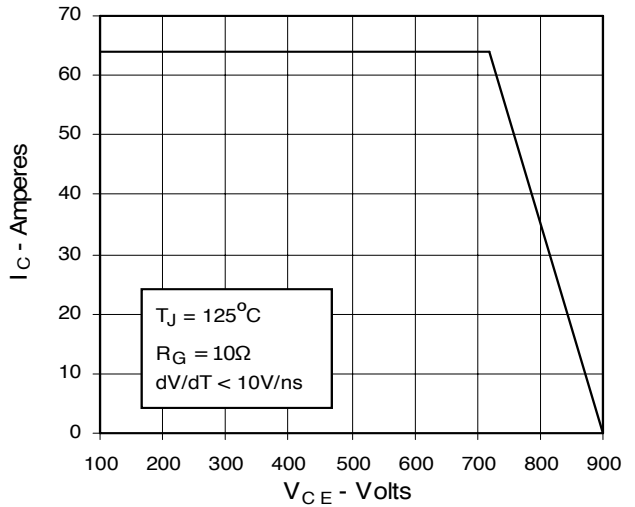


Fig. 11. Maximum Transient Thermal Resistance

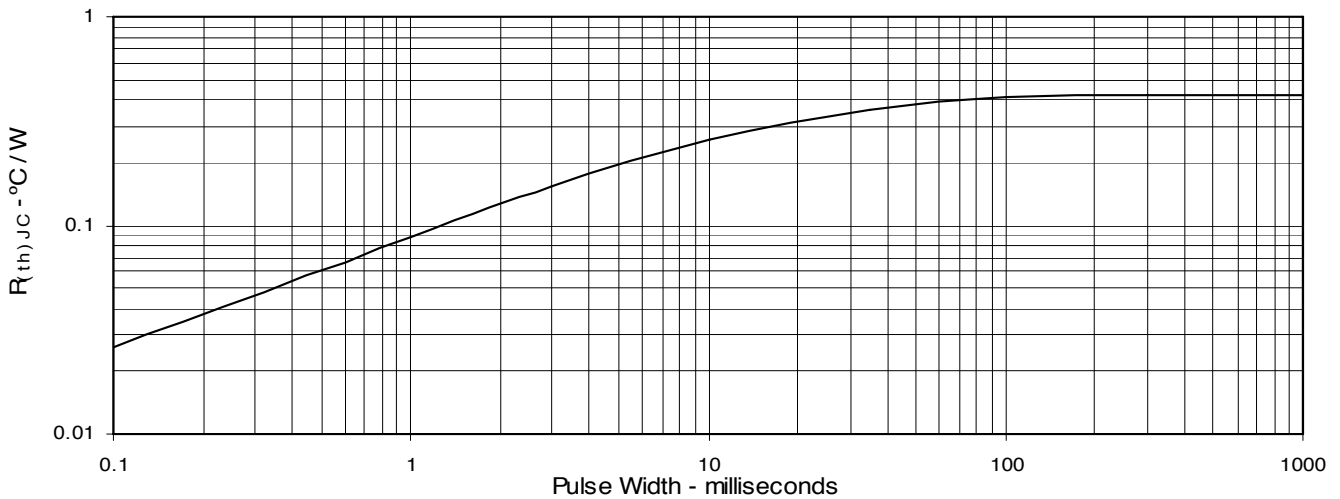


Fig. 12. Dependence of Turn-off Energy Loss on Gate Resistance

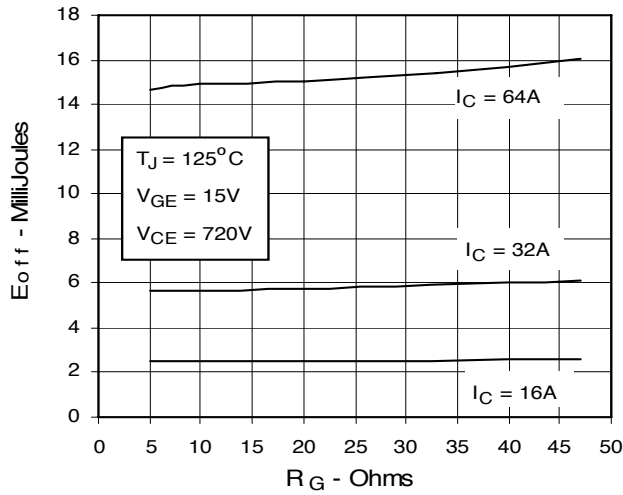


Fig. 13. Dependence of Turn-on Energy Loss on Gate Resistance

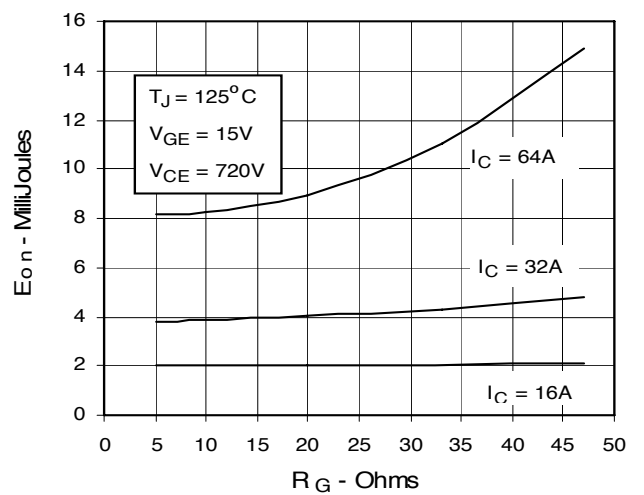


Fig. 14. Dependence of Turn-off Energy Loss on Collector Current

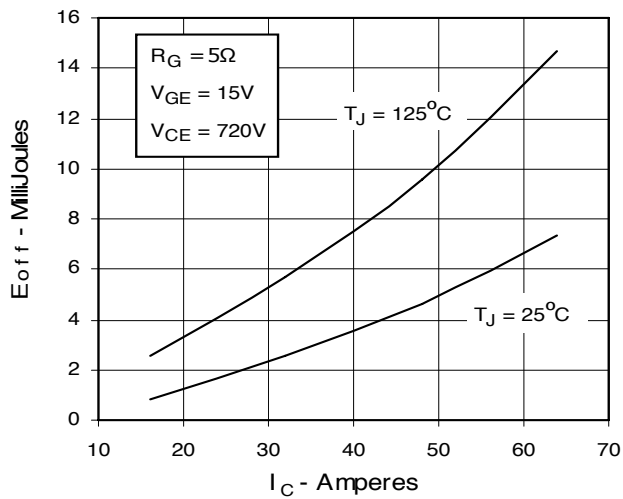


Fig. 15. Dependence of Turn-on Energy Loss on Collector Current

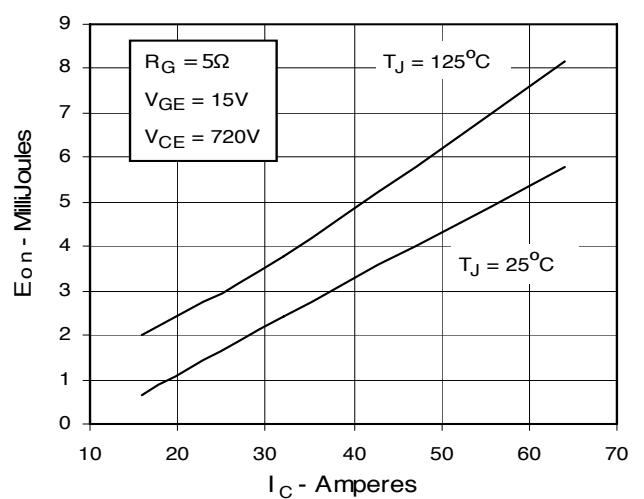


Fig. 16. Dependence of Turn-off Energy Loss on Temperature

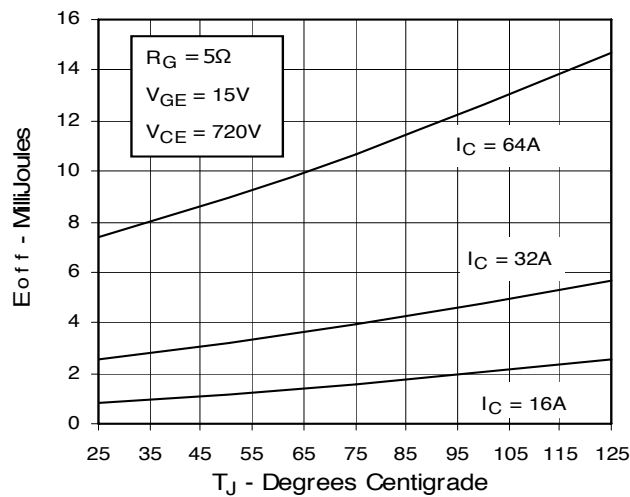


Fig. 17. Dependence of Turn-on Energy Loss on Temperature

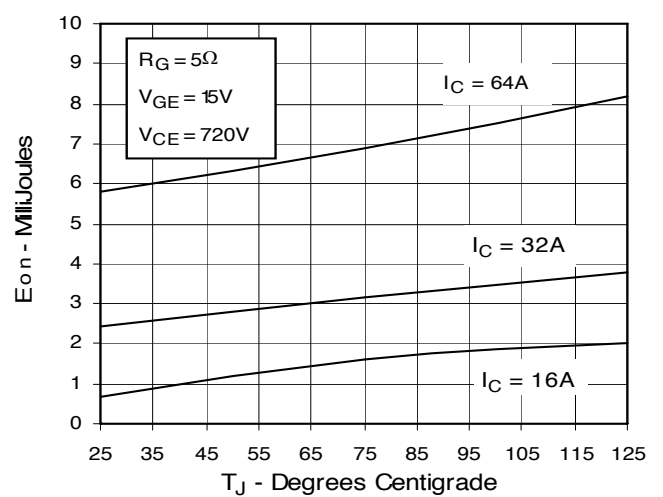


Fig. 18. Dependence of Turn-off Switching Time on Gate Resistance

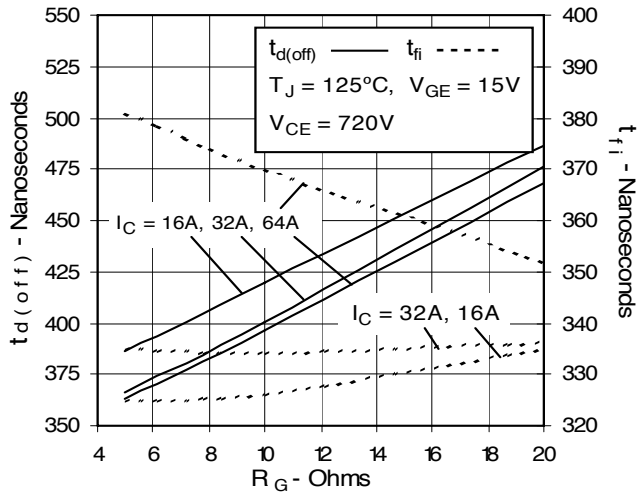


Fig. 19. Dependence of Turn-on Switching Time on Gate Resistance

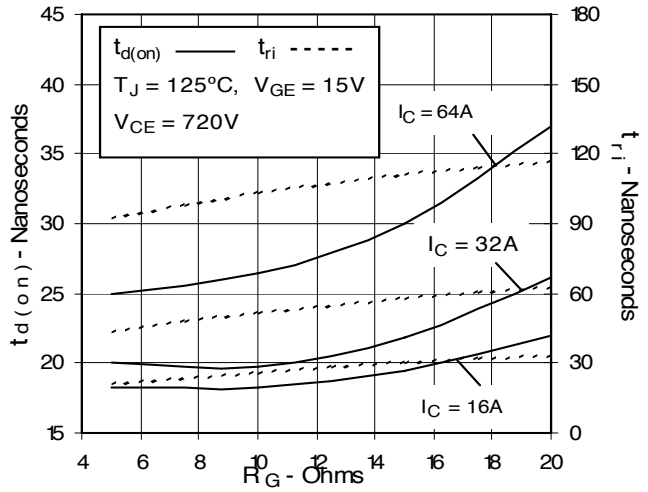


Fig. 20. Dependence of Turn-off Switching Time on Collector Current

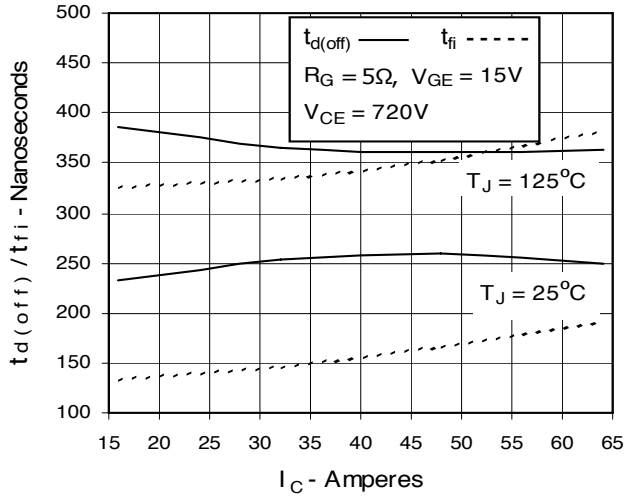


Fig. 21. Dependence of Turn-on Switching Time on Collector Current

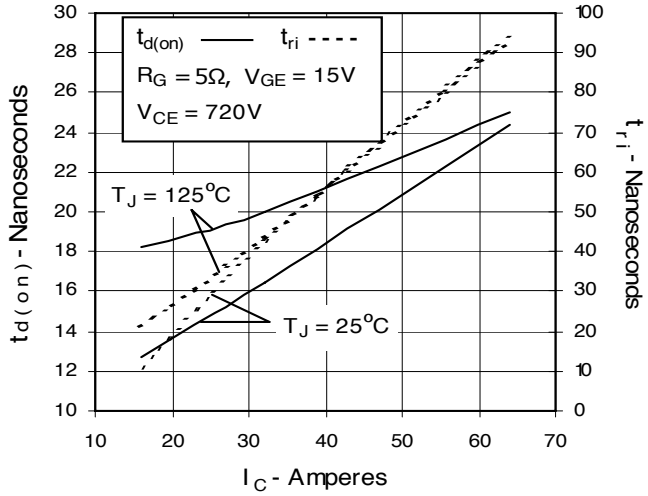


Fig. 22. Dependence of Turn-off Switching Time on Temperature

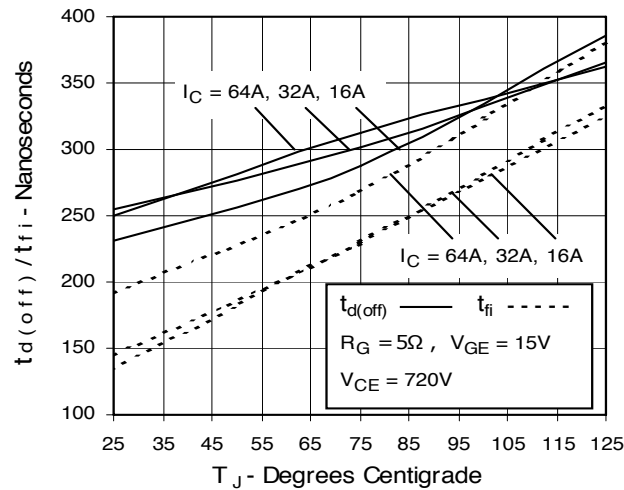
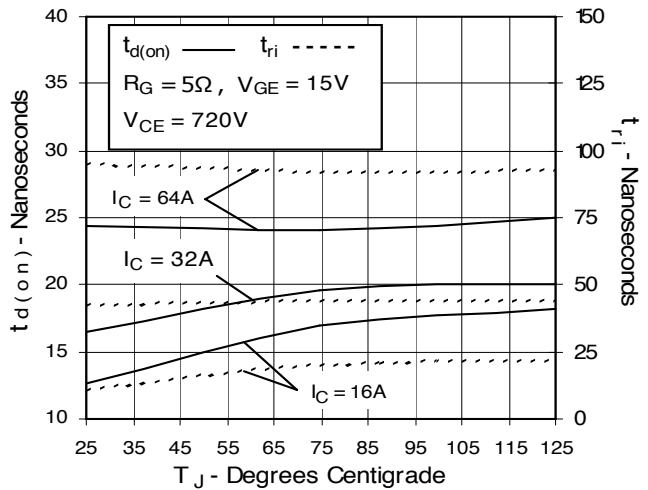


Fig. 23. Dependence of Turn-on Switching Time on Temperature



ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated objective result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.



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